

Smart High-Side Power Switch

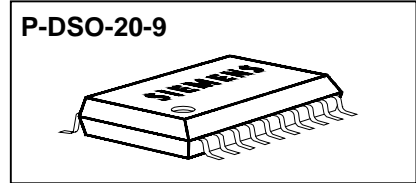
Two Channels: 2 x 30mΩ

Current Sense

Product Summary

Operating Voltage	$V_{bb(on)}$	5.0...34V	
	Active channels	one	two parallel
On-state Resistance	R_{ON}	30mΩ	15mΩ
Nominal load current	$I_{L(NOM)}$	5.5A	8.5A
Current limitation	$I_{L(SCr)}$	24A	24A

Package



General Description

- N channel vertical power MOSFET with charge pump, ground referenced CMOS compatible input, diagnostic feedback and proportional load current sense monolithically integrated in Smart SiPMOS® technology.
- Fully protected by embedded protection functions

Applications

- μ C compatible high-side power switch with diagnostic feedback for 12V and 24V grounded loads
- All types of resistive, inductive and capacitive loads
- Most suitable for loads with high inrush currents, so as lamps
- Replaces electromechanical relays, fuses and discrete circuits

Basic Functions

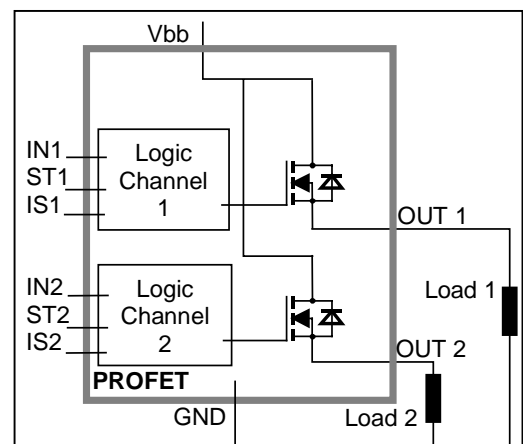
- CMOS compatible input
- Undervoltage and overvoltage shutdown with auto-restart and hysteresis
- Fast demagnetization of inductive loads
- Logic ground independent from load ground

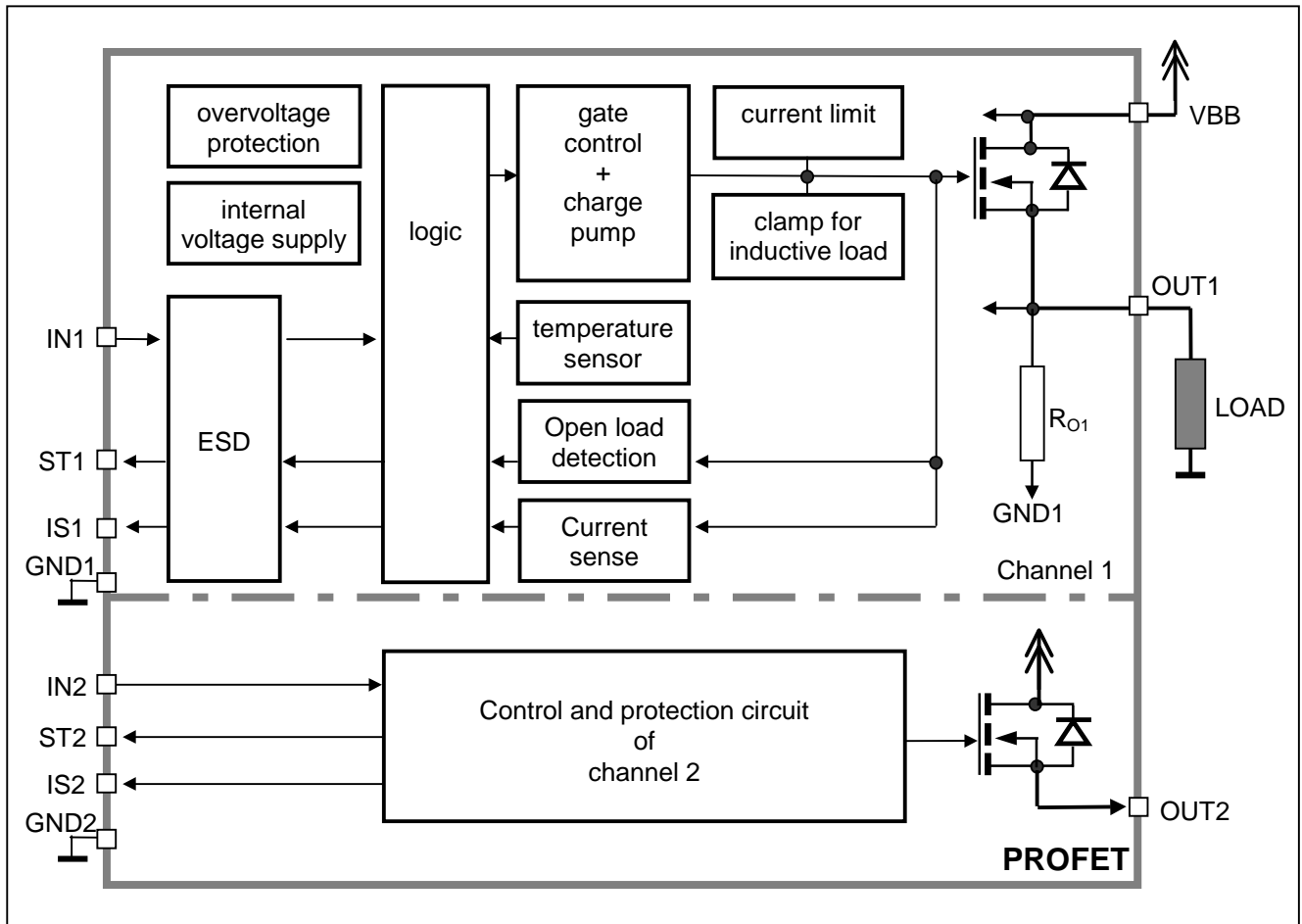
Protection Functions

- Short circuit protection
- Overload protection
- Current limitation
- Thermal shutdown
- Overvoltage protection (including load dump) with external resistor
- Reverse battery protection with external resistor
- Loss of ground and loss of V_{bb} protection
- Electrostatic discharge protection (ESD)

Diagnostic Functions

- Proportional load current sense
- Diagnostic feedback with open drain output
- Open load detection in OFF-state with external resistor
- Feedback of thermal shutdown in ON-state

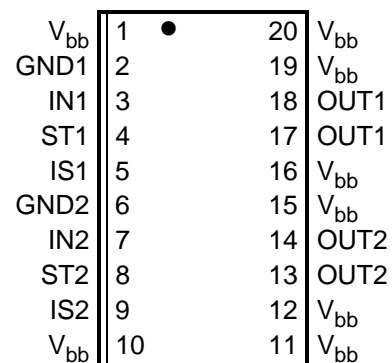


Functional diagram

Pin Definitions and Functions

Pin	Symbol	Function
1,10, 11,12, 15,16, 19,20	V_{bb}	Positive power supply voltage. Design the wiring for the simultaneous max. short circuit currents from channel 1 to 2 and also for low thermal resistance
3	IN1	Input 1,2, activates channel 1,2 in case of logic high signal
7	IN2	
17,18	OUT1	Output 1,2, protected high-side power output of channel 1,2. Both pins of each output have to be connected in parallel for operation according this spec (e.g. k_{IIS}). Design the wiring for the max. short circuit current
13,14	OUT2	
4	ST1	Diagnostic feedback 1,2 of channel 1,2, open drain, invers to input level
8	ST2	
2	GND1	Ground 1 of chip 1 (channel 1)
6	GND2	Ground 2 of chip 2 (channel 2)
5	IS1	Sense current output 1,2; proportional to the load current, zero in the case of current limitation of the load current
9	IS2	

Pin configuration

(top view)



Maximum Ratings at $T_j = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 4)	V_{bb}	43	V
Supply voltage for full short circuit protection $T_{j,start} = -40 \dots +150^\circ\text{C}$	V_{bb}	34	V
Load current (Short-circuit current, see page 5)	I_L	self-limited	A
Load dump protection ¹⁾ $V_{LoadDump} = V_A + V_S$, $V_A = 13.5\text{ V}$ $R_1^{2)} = 2\ \Omega$, $t_{di} = 200\text{ ms}$; $I_N = \text{low or high}$, each channel loaded with $R_L = 7.0\ \Omega$,	$V_{Load\ dump}^{3)}$	60	V
Operating temperature range	T_j	$-40 \dots +150$	$^\circ\text{C}$
Storage temperature range	T_{stg}	$-55 \dots +150$	$^\circ\text{C}$
Power dissipation (DC) ⁴⁾ (all channels active)	$T_a = 25^\circ\text{C}$: $T_a = 85^\circ\text{C}$: P_{tot}	3.8 2.0	W
Maximal switchable inductance, single pulse $V_{bb} = 12\text{V}$, $T_{j,start} = 150^\circ\text{C}^4)$, $I_L = 5.5\text{ A}$, $E_{AS} = 370\text{ mJ}$, $0\ \Omega$ one channel: $I_L = 8.5\text{ A}$, $E_{AS} = 790\text{ mJ}$, $0\ \Omega$ two parallel channels: see diagrams on page 10	Z_L	18 16	mH
Electrostatic discharge capability (ESD) (Human Body Model) I_N : ST, IS: out to all other pins shorted: acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993 $R = 1.5\text{k}\Omega$; $C = 100\text{pF}$	V_{ESD}	1.0 4.0 8.0	kV
Input voltage (DC)	V_{IN}	$-10 \dots +16$	V
Current through input pin (DC)	I_{IN}	± 2.0	mA
Current through status pin (DC)	I_{ST}	± 5.0	
Current through current sense pin (DC) see internal circuit diagram page 9	I_{IS}	± 14	

Thermal Characteristics

Parameter and Conditions	Symbol	Values			Unit
		min	typ	Max	
Thermal resistance junction - soldering point ^{4),5)} each channel: junction - ambient ⁴⁾ one channel active: all channels active:	R_{thjs} R_{thja}	-- -- --	-- 40 33	12 -- --	K/W

1) Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins (a $150\ \Omega$ resistor for the GND connection is recommended).

2) R_1 = internal resistance of the load dump test pulse generator

3) $V_{Load\ dump}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

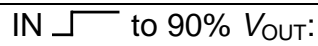
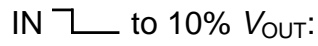
4) Device on $50\text{mm} \times 50\text{mm} \times 1.5\text{mm}$ epoxy PCB FR4 with 6cm^2 (one layer, $70\ \mu\text{m}$ thick) copper area for V_{bb} connection. PCB is vertical without blown air. See page 15

5) Soldering point: upper side of solder edge of device pin 15. See page 15

Electrical Characteristics

Parameter and Conditions, each of the two channels at $T_j = -40\dots+150^\circ\text{C}$, $V_{bb} = 12\text{ V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

Load Switching Capabilities and Characteristics

On-state resistance (V_{bb} to OUT); $I_L = 5\text{ A}$ each channel, $T_j = 25^\circ\text{C}$: $T_j = 150^\circ\text{C}$: two parallel channels, $T_j = 25^\circ\text{C}$:	R_{ON}	--	27 54 14	30 60 15	m Ω
Output voltage drop limitation at small load currents, see page 14 $I_L = 0.5\text{ A}$ $T_j = -40\dots+150^\circ\text{C}$:	$V_{ON(NL)}$	--	50	--	mV
Nominal load current one channel active: two parallel channels active: Device on PCB ⁶⁾ , $T_a = 85^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$	$I_{L(NOM)}$	4.9 7.8	5.5 8.5	--	A
Output current while GND disconnected or pulled up; $V_{bb} = 30\text{ V}$, $V_{IN} = 0$, see diagram page 9; (not tested specified by design)	$I_{L(GNDhigh)}$	--	--	8	mA
Turn-on time ⁷⁾ IN  to 90% V_{OUT} :	t_{on}	25	70	150	μs
Turn-off time IN  to 10% V_{OUT} : $R_L = 12\ \Omega$	t_{off}	25	80	200	
Slew rate on ⁷⁾ 10 to 30% V_{OUT} , $R_L = 12\ \Omega$:	dV/dt_{on}	0.1	--	1	V/ μs
Slew rate off ⁷⁾ 70 to 40% V_{OUT} , $R_L = 12\ \Omega$:	$-dV/dt_{off}$	0.1	--	1	V/ μs

Operating Parameters

Operating voltage ⁸⁾	$V_{bb(on)}$	5.0	--	34	V
Undervoltage shutdown	$V_{bb(under)}$	3.2	--	5.0	V
Undervoltage restart $T_j = -40\dots+25^\circ\text{C}$: $T_j = +150^\circ\text{C}$:	$V_{bb(u\ rst)}$	--	4.5	5.5 6.0	V
Undervoltage restart of charge pump see diagram page 13 $T_j = -40\dots+25^\circ\text{C}$: $T_j = 150^\circ\text{C}$:	$V_{bb(ucp)}$	--	4.7 --	6.5 7.0	V
Undervoltage hysteresis $\Delta V_{bb(under)} = V_{bb(u\ rst)} - V_{bb(under)}$	$\Delta V_{bb(under)}$	--	0.5	--	V
Overvoltage shutdown	$V_{bb(over)}$	34	--	43	V
Overvoltage restart	$V_{bb(o\ rst)}$	33	--	--	V
Overvoltage hysteresis	$\Delta V_{bb(over)}$	--	1	--	V

⁶⁾ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for V_{bb} connection. PCB is vertical without blown air. See page 15

⁷⁾ See timing diagram on page 11.

⁸⁾ At supply voltage increase up to $V_{bb} = 4.7\text{ V}$ typ without charge pump, $V_{OUT} \approx V_{bb} - 2\text{ V}$

Parameter and Conditions, each of the two channels at $T_j = -40\dots+150^\circ\text{C}$, $V_{bb} = 12\text{ V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	
Overvoltage protection ⁹⁾ $I_{bb}=40\text{ mA}$	$T_j = -40^\circ\text{C}$: $T_j = +25\dots+150^\circ\text{C}$: $V_{bb(AZ)}$	41 43	-- 47	-- 52	V
Standby current ¹⁰⁾ $V_{IN} = 0$; see diagram page 10	$T_j = -40^\circ\text{C}\dots25^\circ\text{C}$: $T_j = 150^\circ\text{C}$: $I_{bb(off)}$	-- --	8 24	30 50	μA
Leakage output current (included in $I_{bb(off)}$) $V_{IN} = 0$	$I_{L(off)}$	--	--	20	μA
Operating current ¹¹⁾ , $V_{IN} = 5\text{V}$, $I_{GND} = I_{GND1} + I_{GND2}$, one channel on: two channels on:	I_{GND}	-- --	1.2 2.4	3 6	mA

Protection Functions

Current limit, (see timing diagrams, page 12)	$T_j = -40^\circ\text{C}$: $T_j = 25^\circ\text{C}$: $T_j = +150^\circ\text{C}$: $I_{L(lim)}$	48 40 31	56 50 37	65 58 45	A
Repetitive short circuit current limit, $T_j = T_{jt}$ each channel two parallel channels (see timing diagrams, page 12)	$I_{L(SCr)}$	-- --	24 24	-- --	A
Initial short circuit shutdown time (see timing diagrams on page 12)	$T_{j,start} = 25^\circ\text{C}$: $t_{off(SC)}$	--	2.0	--	ms
Output clamp (inductive load switch off) ¹²⁾ at $V_{ON(CL)} = V_{bb} - V_{OUT}$, $I_L = 40\text{ mA}$	$T_j = -40^\circ\text{C}$: $T_j = 25^\circ\text{C}\dots150^\circ\text{C}$: $V_{ON(CL)}$	41 43	-- 47	-- 52	V
Thermal overload trip temperature	T_{jt}	150	--	--	$^\circ\text{C}$
Thermal hysteresis	ΔT_{jt}	--	10	--	K

Reverse Battery

Reverse battery voltage ¹³⁾	$-V_{bb}$	--	--	32	V
Drain-source diode voltage ($V_{out} > V_{bb}$) $I_L = -4.0\text{ A}$, $T_j = +150^\circ\text{C}$	$-V_{ON}$	--	600	--	mV

9) Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins (a $150\ \Omega$ resistor in the GND connection is recommended). See also $V_{ON(CL)}$ in table of protection functions and circuit diagram page 9.

10) Measured with load; for the whole device; all channels off




11) Add I_{ST} , if $I_{ST} > 0$

12) If channels are connected in parallel, output clamp is usually accomplished by the channel with the lowest $V_{ON(CL)}$

13) Requires a $150\ \Omega$ resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Power dissipation is higher compared to normal operating conditions due to the voltage drop across the drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 3 and circuit page 9).

Parameter and Conditions, each of the two channels at $T_j = -40...+150^\circ\text{C}$, $V_{bb} = 12\text{ V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

Diagnostic Characteristics

Current sense ratio ¹⁴), static on-condition, $V_{IS} = 0...5\text{ V}$, $V_{bb(\text{on})} = 6.5^{15})...27\text{V}$, $k_{ILIS} = I_L / I_{IS}$	$T_j = -40^\circ\text{C}$, $I_L = 5\text{ A}$: $T_j = -40^\circ\text{C}$, $I_L = 0.5\text{ A}$: $T_j = 25...+150^\circ\text{C}$, $I_L = 5\text{ A}$: $T_j = 25...+150^\circ\text{C}$, $I_L = 0.5\text{ A}$:	k_{ILIS}	4350 3100 4350 3800	4800 4800 4800 4800	5800 7800 5350 6300	
Current sense output voltage limitation $T_j = -40 \dots +150^\circ\text{C}$	$I_{IS} = 0$, $I_L = 5\text{ A}$:	$V_{IS(\text{lim})}$	5.4	6.1	6.9	V
Current sense leakage/offset current $T_j = -40 \dots +150^\circ\text{C}$	$V_{IN}=0$, $V_{IS} = 0$, $I_L = 0$: $V_{IN}=5\text{ V}$, $V_{IS} = 0$, $I_L = 0$: $V_{IN}=5\text{ V}$, $V_{IS} = 0$, $V_{OUT} = 0$ (short circuit) ($I_{IS}(\text{SH})$ not tested, specified by design)	$I_{IS(\text{LL})}$ $I_{IS(\text{LH})}$ $I_{IS(\text{SH})}$	0 0 0	-- -- --	1 15 10	μA
Current sense settling time to $I_{IS\text{ static}} \pm 10\%$ after positive input slope, $I_L = 0 \rightarrow 5\text{ A}$ (not tested, specified by design)		$t_{\text{son}(IS)}$	--	--	300	μs
Current sense settling time to 10% of $I_{IS\text{ static}}$ after negative input slope, $I_L = 5 \rightarrow 0\text{ A}$ (not tested, specified by design)		$t_{\text{soff}(IS)}$	--	30	100	μs
Current sense rise time (60% to 90%) after change of load current $I_L = 2.5 \rightarrow 5\text{ A}$ (not tested, specified by design)		$t_{\text{slc}(IS)}$	--	10	--	μs
Open load detection voltage ¹⁶) (off-condition)		$V_{OUT(\text{OL})}$	2	3	4	V
Internal output pull down (pin 17,18 to 2 resp. 13,14 to 6), $V_{OUT}=5\text{ V}$		R_O	5	15	40	$\text{k}\Omega$

¹⁴) This range for the current sense ratio refers to all devices. The accuracy of the k_{ILIS} can be raised at least by a factor of two by matching the value of k_{ILIS} for every single device.



In the case of current limitation the sense current I_{IS} is zero and the diagnostic feedback potential V_{ST} is High. See figure 2c, page 12.

¹⁵) Valid if $V_{bb(\text{u rst})}$ was exceeded before.

¹⁶) External pull up resistor required for open load detection in off state.

Parameter and Conditions, each of the two channels at $T_j = -40\dots+150^\circ\text{C}$, $V_{bb} = 12\text{ V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

Input and Status Feedback¹⁷⁾

Input resistance (see circuit page 9)	R_I	3.0	4.5	7.0	k Ω
Input turn-on threshold voltage 	$V_{IN(T+)}$	--	--	3.5	V
Input turn-off threshold voltage 	$V_{IN(T-)}$	1.5	--	--	V
Input threshold hysteresis	$\Delta V_{IN(T)}$	--	0.5	--	V
Off state input current $V_{IN} = 0.4\text{ V}$:	$I_{IN(off)}$	1	--	50	μA
On state input current $V_{IN} = 5\text{ V}$:	$I_{IN(on)}$	20	50	90	μA
Delay time for status with open load after Input neg. slope (see diagram page 13)	$t_{d(ST\ OL3)}$	--	400	--	μs
Status delay after positive input slope (not tested, specified by design)	$t_{don(ST)}$	--	13	--	μs
Status delay after negative input slope (not tested, specified by design)	$t_{doff(ST)}$	--	1	--	μs
Status output (open drain)					
Zener limit voltage $T_j = -40\dots+150^\circ\text{C}$, $I_{ST} = +1.6\text{ mA}$:	$V_{ST(high)}$	5.4	6.1	6.9	V
ST low voltage $T_j = -40\dots+25^\circ\text{C}$, $I_{ST} = +1.6\text{ mA}$:	$V_{ST(low)}$	--	--	0.4	
$T_j = +150^\circ\text{C}$, $I_{ST} = +1.6\text{ mA}$:		--	--	0.7	
Status leakage current, $V_{ST} = 5\text{ V}$, $T_j = 25 \dots +150^\circ\text{C}$:	$I_{ST(high)}$	--	--	2	μA

¹⁷⁾ If ground resistors R_{GND} are used, add the voltage drop across these resistors.

Truth Table

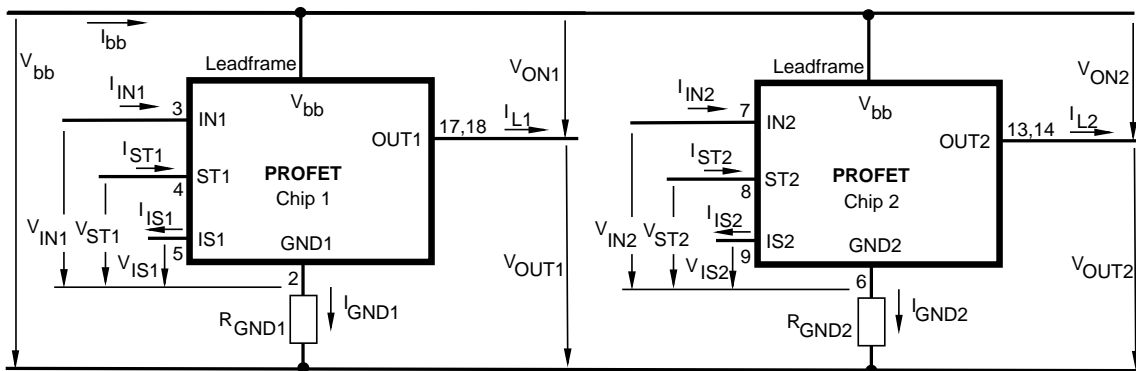
	Input 1	Output 1	Status 1	Current Sense 1
	Input 2	Output 2	Status 2	Current Sense 2
	level	level	level	I_{IS}
Normal operation	L	L	H	0
	H	H	L	nominal
Current-limitation	L	L	H	0
	H	H	H	0
Short circuit to GND	L	L	H	0
	H	L ¹⁸⁾	H	0
Over-temperature	L	L	H	0
	H	L	H	0
Short circuit to V _{bb}	L	H	L ¹⁹⁾	0
	H	H	L	<nominal ²⁰⁾
Open load	L	L ²¹⁾	H (L ²²⁾)	0
	H	H	L	0
Undervoltage	L	L	H	0
	H	L	L	0
Overvoltage	L	L	H	0
	H	L	L	0
Negative output voltage clamp	L	L	H	0

L = "Low" Level X = don't care Z = high impedance, potential depends on external circuit

H = "High" Level Status signal after the time delay shown in the diagrams (see fig 5. page 13)

Parallel switching of channel 1 and 2 is possible by connecting the inputs and outputs in parallel. The status outputs ST1 and ST2 have to be configured as a 'Wired OR' function with a single pull-up resistor. The current sense outputs IS1 and IS2 have to be connected with a single pull-down resistor.

Terms

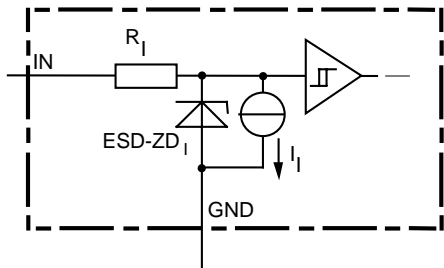


Leadframe (V_{bb}) is connected to pin 1,10,11,12,15,16,19,20

External R_{GND} optional; two resistors R_{GND1} , $R_{GND2} = 150 \Omega$ or a single resistor $R_{GND} = 75 \Omega$ for reverse battery protection up to the max. operating voltage.

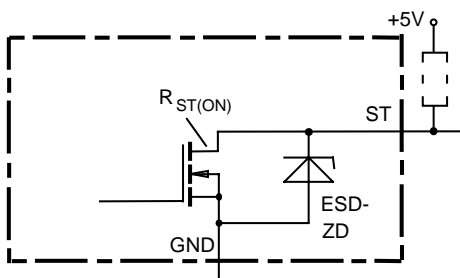
- 18) The voltage drop over the power transistor is $V_{bb} - V_{OUT} > 3V$ typ. Under this condition the sense current I_{IS} is zero
- 19) An external short of output to V_{bb} , in the off state, causes an internal current from output to ground. If R_{GND} is used, an offset voltage at the GND and ST pins will occur and the $V_{ST\ low}$ signal may be erroneous.
- 20) Low ohmic short to V_{bb} may reduce the output current I_L and therefore also the sense current I_{IS} .
- 21) Power Transistor off, high impedance
- 22) with external resistor between V_{BB} and OUT

Input circuit (ESD protection), IN1 or IN2



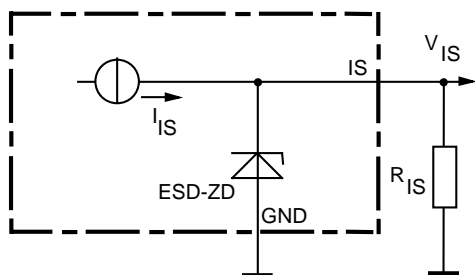
The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Status output, ST1 or ST2



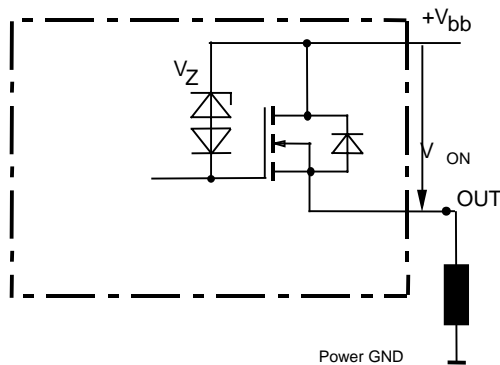
ESD-Zener diode: 6.1 V typ., max 5.0 mA; $R_{ST(ON)} < 375 \Omega$ at 1.6 mA. The use of ESD zener diodes as voltage clamp at DC conditions is not recommended.

Current sense output



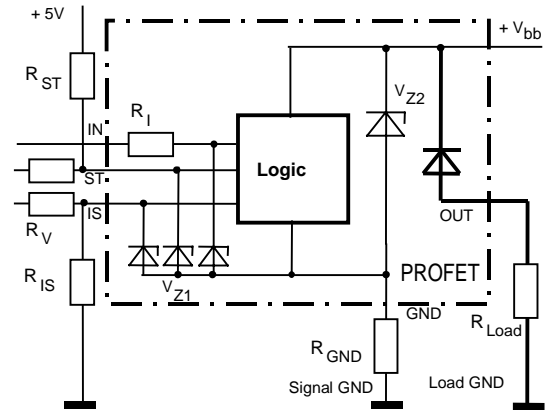
ESD-Zener diode: 6.1 V typ., max 14 mA; $R_{IS} = 1 \text{ k}\Omega$ nominal

Inductive and overvoltage output clamp, OUT1 or OUT2



V_{ON} clamped to $V_{ON(CL)} = 47 \text{ V}$ typ.

Overvoltage and reverse batt. protection

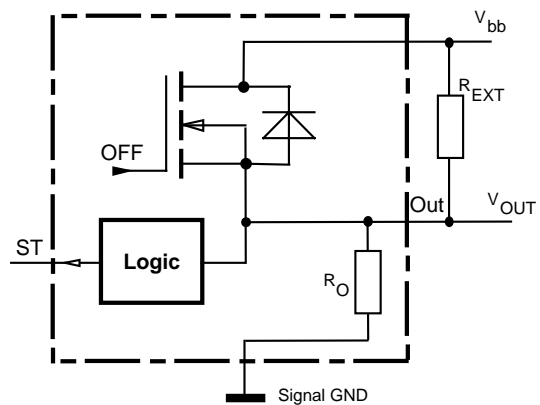


$V_{Z1} = 6.1 \text{ V}$ typ., $V_{Z2} = 47 \text{ V}$ typ., $R_{GND} = 150 \Omega$, $R_{ST} = 15 \text{ k}\Omega$, $R_I = 4.5 \text{ k}\Omega$ typ., $R_{IS} = 1 \text{ k}\Omega$, $R_V = 15 \text{ k}\Omega$, In case of reverse battery the current has to be limited by the load. Temperature protection is not active

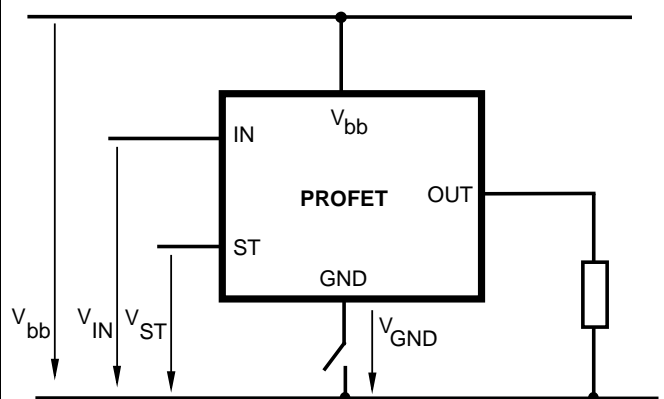
Open-load detection OUT1 or OUT2

OFF-state diagnostic condition:

$V_{OUT} > 3 \text{ V}$ typ.; IN low

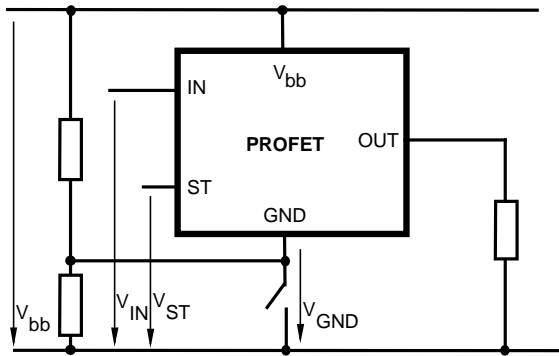


GND disconnect



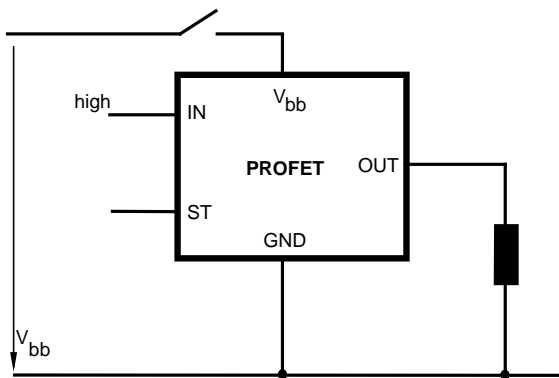
Any kind of load. In case of IN = high is $V_{OUT} \approx V_{IN} - V_{IN(T+)}$. Due to $V_{GND} > 0$, no $V_{ST} = \text{low}$ signal available.

GND disconnect with GND pull up



Any kind of load. If $V_{GND} > V_{IN} - V_{IN(T+)}$ device stays off
 Due to $V_{GND} > 0$, no V_{ST} = low signal available.

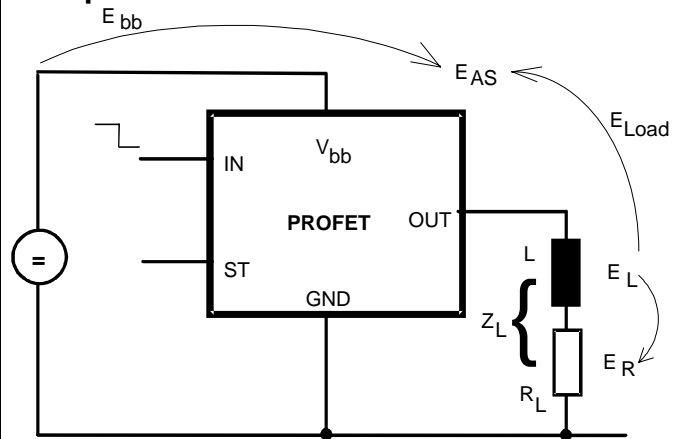
V_{bb} disconnect with energized inductive load



For inductive load currents up to the limits defined by Z_L (max. ratings and diagram on page 10) each switch is protected against loss of V_{bb} .

Consider at your PCB layout that in the case of V_{bb} disconnection with energized inductive load all the load current flows through the GND connection.

Inductive load switch-off energy dissipation



Energy stored in load inductance:

$$E_L = 1/2 \cdot L \cdot I_L^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

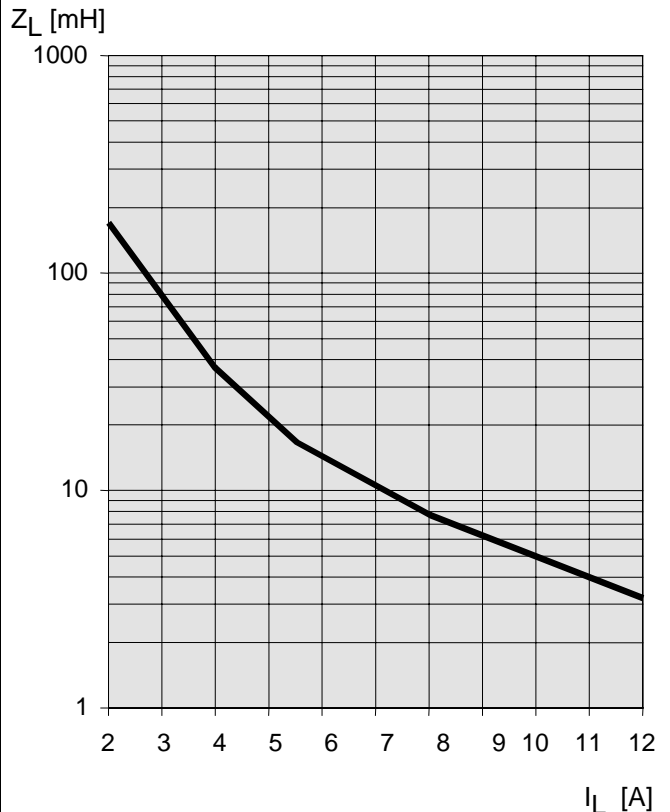
$$E_{AS} = E_{bb} + E_L - E_R = \int V_{ON(CL)} \cdot i_L(t) dt,$$

with an approximate solution for $R_L > 0 \Omega$:

$$E_{AS} = \frac{I_L \cdot L}{2 \cdot R_L} (V_{bb} + |V_{OUT(CL)}|) \ln \left(1 + \frac{I_L \cdot R_L}{|V_{OUT(CL)}|} \right)$$

Maximum allowable load inductance for a single switch off (one channel)⁴⁾

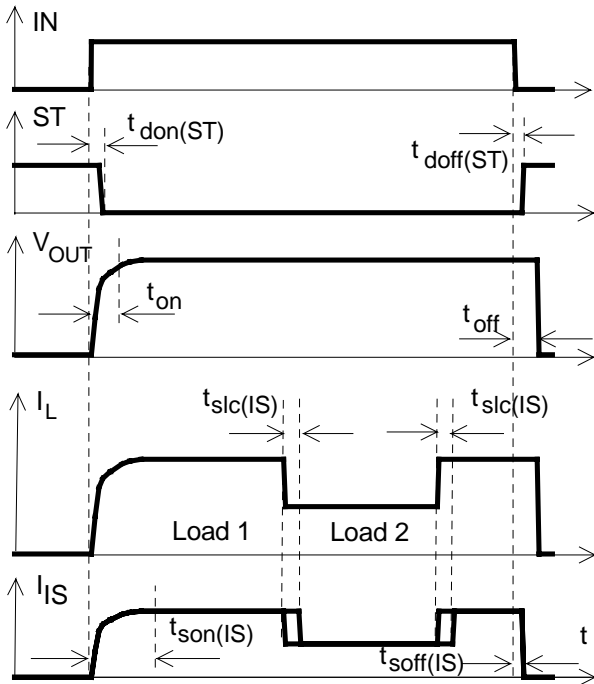
$$L = f(I_L); T_{j,start} = 150^\circ C, V_{bb} = 12 V, R_L = 0 \Omega$$



Timing diagrams

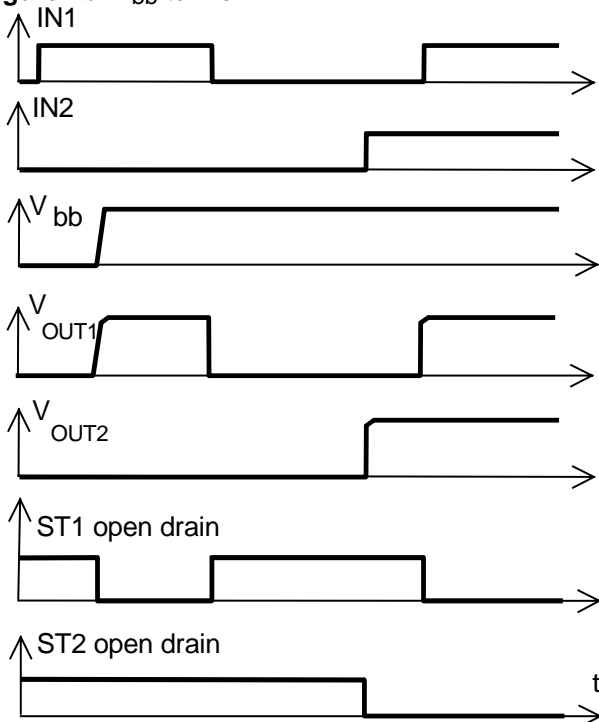
Both channels are symmetric and consequently the diagrams are valid for channel 1 and channel 2

Figure 1a: Switching a resistive load, change of load current in on-condition:



The sense signal is not valid during settling time after turn or change of load current.

Figure 1b: V_{bb} turn on:



proper turn on under all conditions

Figure 2a: Switching a resistive load, turn-on/off time and slew rate definition:

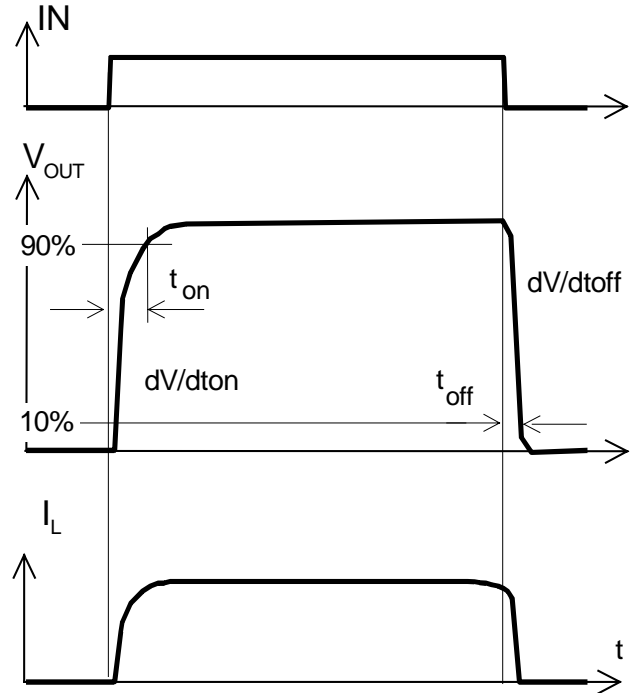
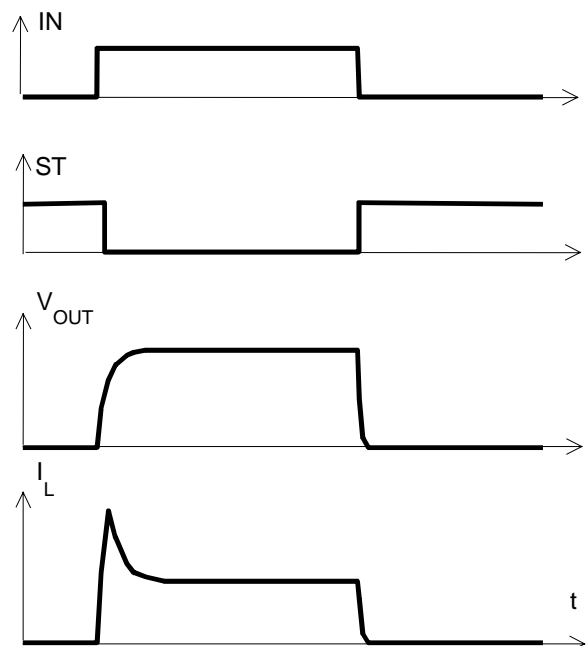


Figure 2b: Switching a lamp:



The initial peak current should be limited by the lamp and not by the current limit of the device.

Figure 2c: Switching a lamp with current limit:

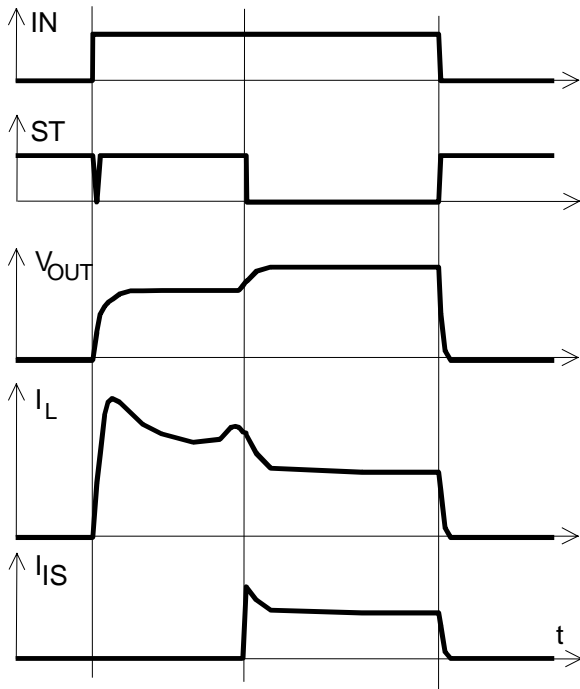
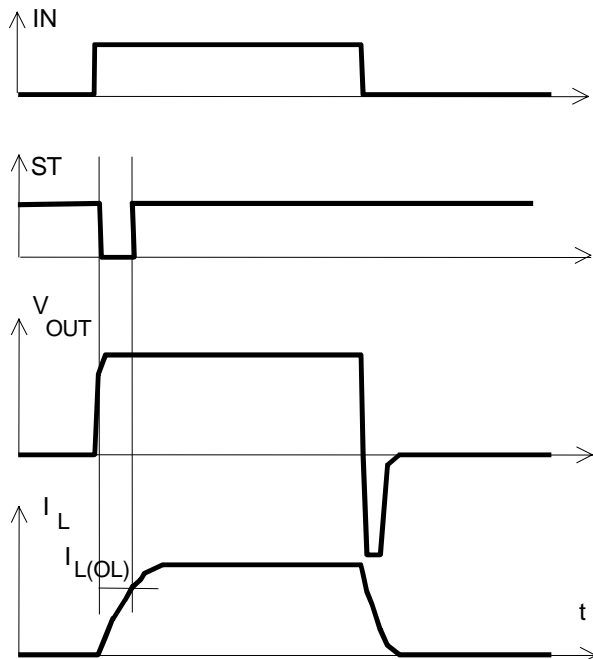
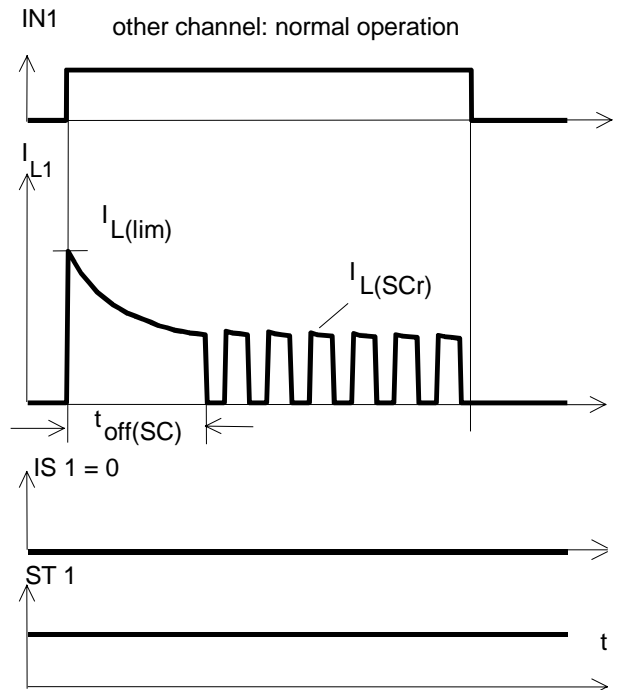


Figure 2d: Switching an inductive load



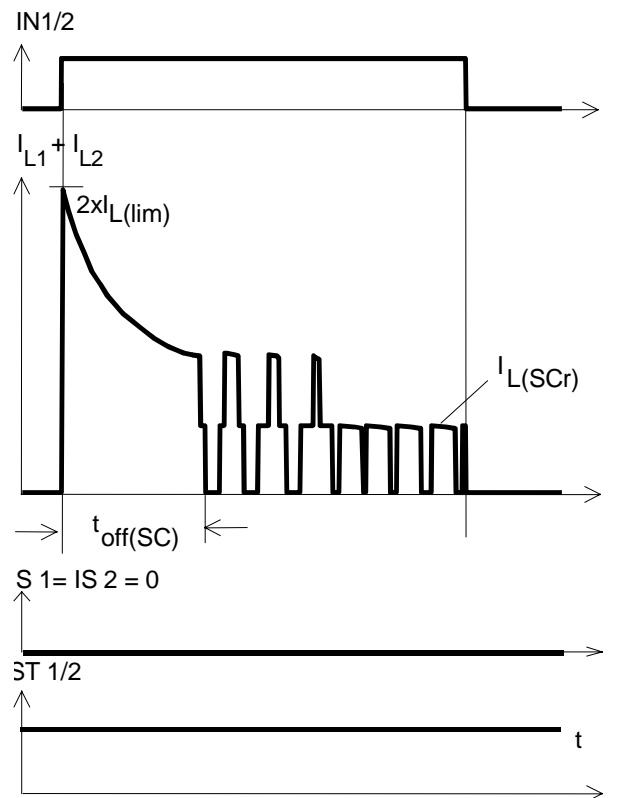
*) if the time constant of load is too large, open-load-status may occur

Figure 3a: Turn on into short circuit: shut down by overtemperature, restart by cooling



Heating up of the chip may require several milliseconds, depending on external conditions

Figure 3b: Turn on into short circuit: shut down by overtemperature, restart by cooling (two parallel switched channels 1 and 2)



ST1 and ST2 have to be configured as a 'Wired OR' function ST1/2 with a single pull-up resistor.

Figure 4a: Overtemperature:
Reset if $T_j < T_{jt}$

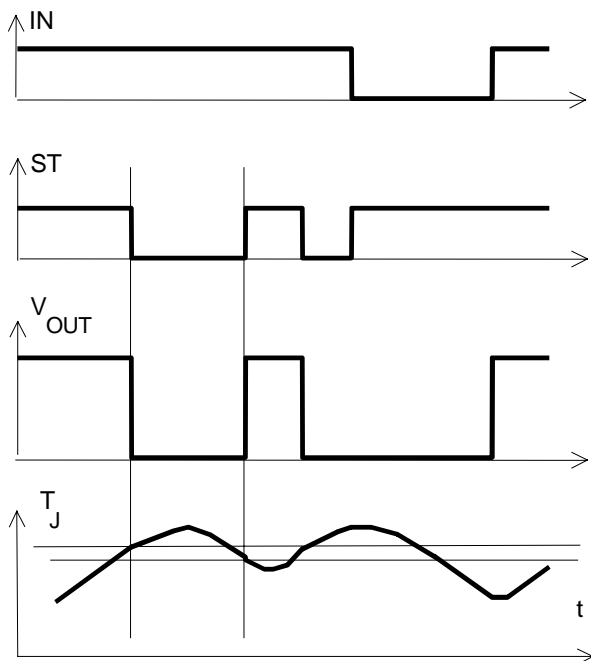


Figure 5a: Open load: detection (with R_{EXT}),
turn on/off to open load

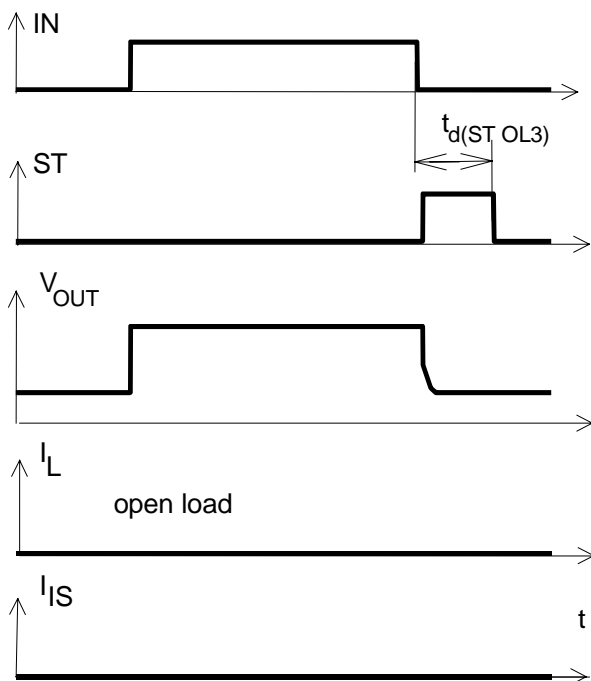


Figure 6a: Undervoltage:

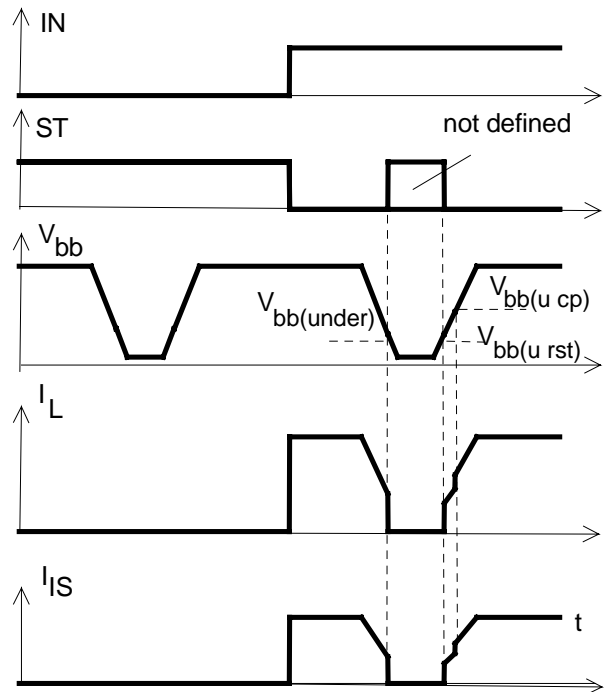


Figure 6b: Undervoltage restart of charge pump

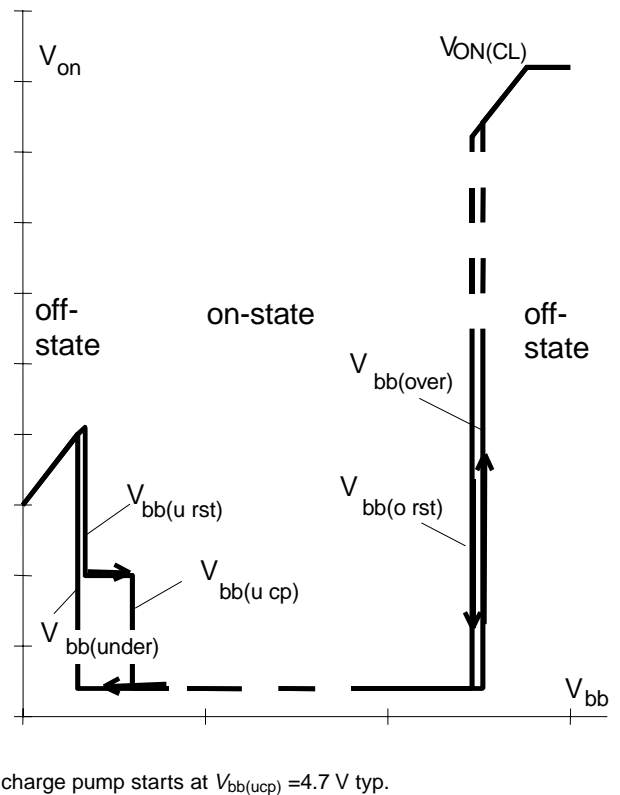


Figure 7a: Overvoltage:

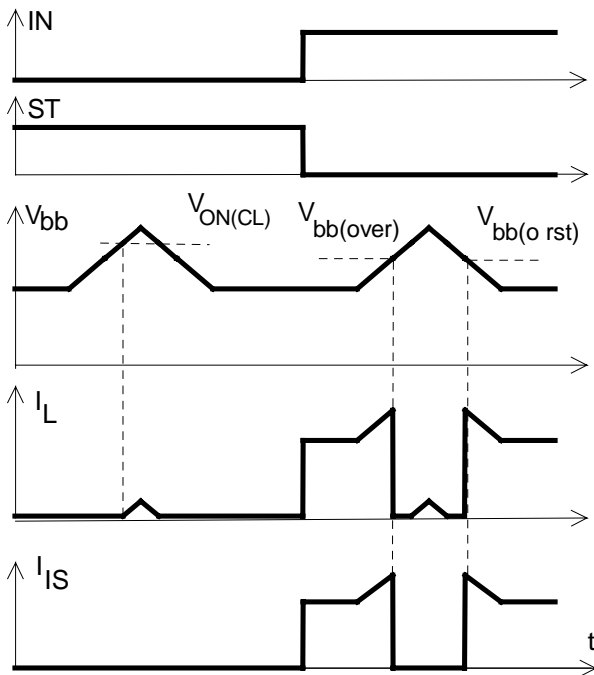


Figure 8b: Current sense ratio:

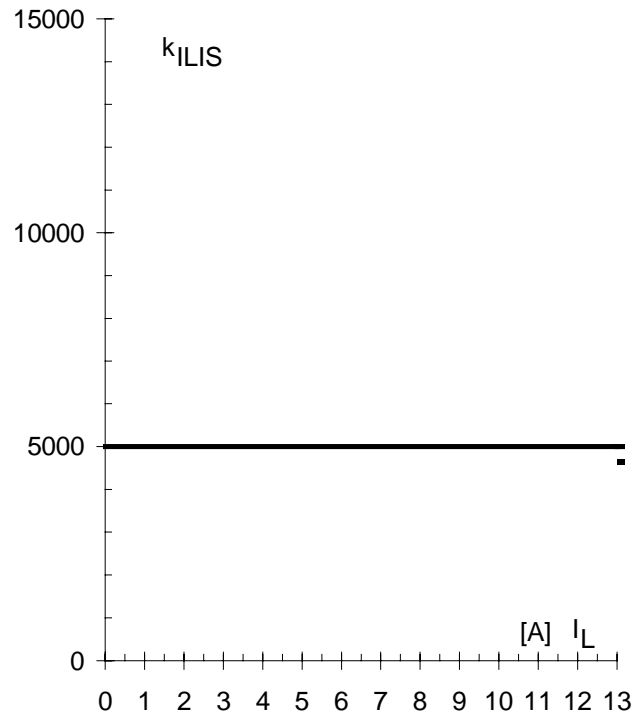


Figure 8a: Current sense versus load current²³:

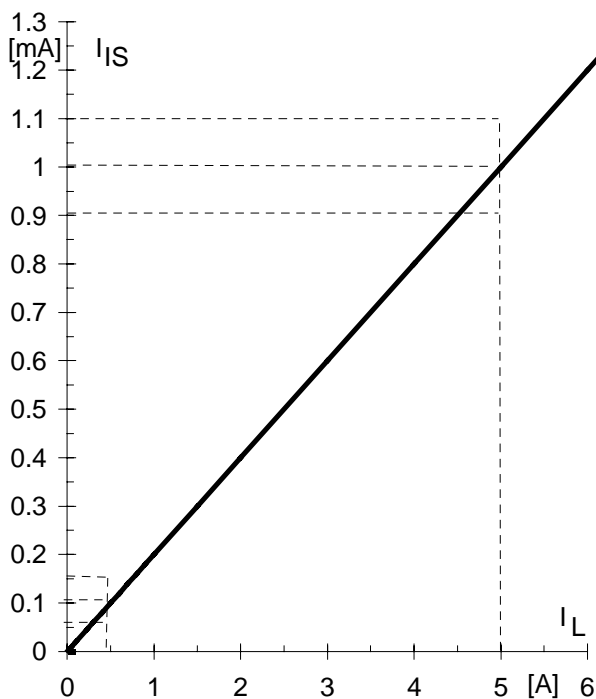
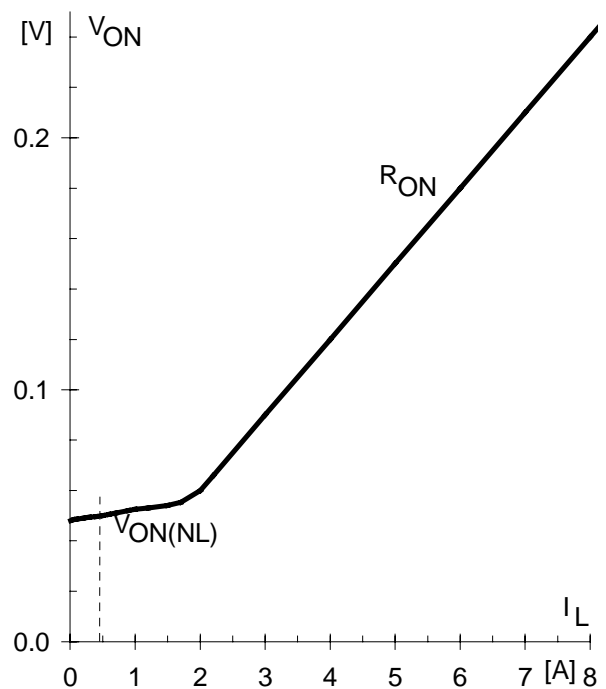


Figure 9a: Output voltage drop versus load current:



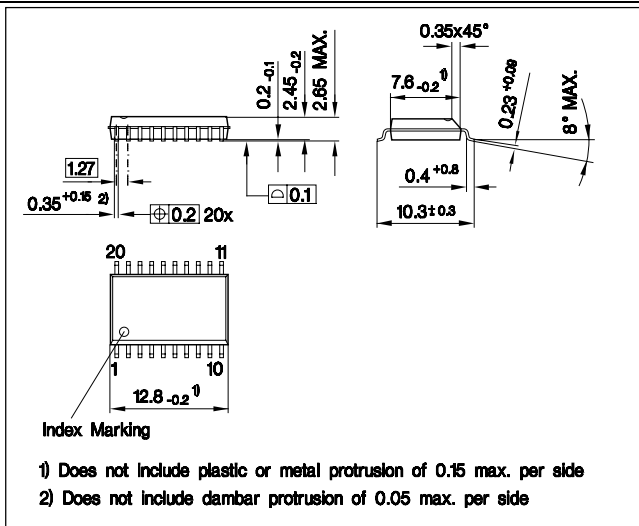
²³ This range for the current sense ratio refers to all devices. The accuracy of the k_{ILIS} can be raised at least by a factor of two by matching the value of k_{ILIS} for every single device.

Package and Ordering Code

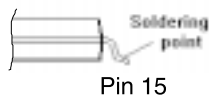
Standard: P-DSO-20-9

Sales Code	BTS 740 L2
Ordering Code	Q67060-S7012-A2

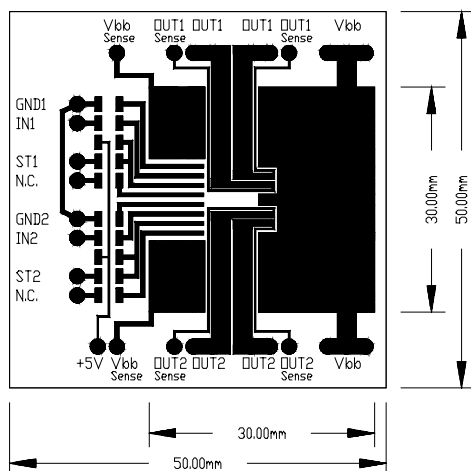
All dimensions in millimetres



Definition of soldering point with temperature T_s :
 upper side of solder edge of device pin 15.



Printed circuit board (FR4, 1.5mm thick, one layer
 70 μ m, 6cm² active heatsink area) as a reference for
 max. power dissipation P_{tot} , nominal load current
 $I_{L(NOM)}$ and thermal resistance R_{thja}



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